



20V COMPLEMENTARY LOW SATURATION TRANSISTORS

Description

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of automotive applications.

Mechanical Data

- Case: W-DFN3020-8 (Type B)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu, Solderable per MIL-STD-202, Method 208 @
- Weight: 0.013 grams (Approximate)

Applications

- DC-DC Converters
- Charging Circuits
- Power Switches
- Motor Control
- LED Backlighting Circuits
- Portable Applications

Features

- NPN Transistor
 - BV_{CEO} > 20V
 - I_C = 4.5A Continuous Collector Current
 - Low Saturation Voltage (150mV Max @ 1A)
 - R_{SAT} = 47mΩ for a Low Equivalent On-Resistance
- PNP Transistor
 - $BV_{CEO} > -20V$
 - I_C = -3.5A Continuous Collector Current
 - Low Saturation Voltage (-220mV Max @ -1A)
 - R_{SAT} = 64mΩ for a Low Equivalent On-Resistance
- hFE Characterized up to 6A for High Current Gain Hold Up
- Low Profile 0.8mm High Package for Thin Applications
- R_{θJA} Efficient, 40% Lower than SOT26
- 6mm² Footprint, 50% Smaller than TSOP6 and SOT26
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free, "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

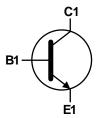
W-DFN3020-8 (Type B)



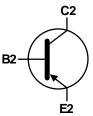




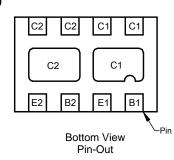
Bottom View



NPN Transistor



PNP Transistor



Equivalent Circuit

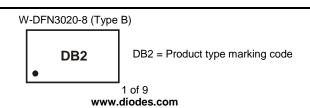
Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
ZXTC6718MCQ-7	Automotive	DB2	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/quality/product_compliance_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information





Absolute Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	NPN PNP		Unit		
Collector-Base Voltage	V_{CBO}	40	-25	V		
Collector-Emitter Voltage	V _{CEO}	20	-20	V		
Emitter-Base Voltage	V_{EBO}	7	-7	V		
Peak Pulse Current		I _{CM}	12	-6	Α	
Continuous Collector Current	(Notes 6 & 9)	1	4.5	-3.5	Λ	
Continuous Collector Current (Notes 7 & 9)		IC	5	-3.8		
Base Current		I _B		1	Α	

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	NPN	PNP	Unit	
	(Notes 6 & 9)		1.5 12 2.45 19.6 1.13 8		W mW/°C
Power Dissipation	(Notes 7 & 9)	D			
Linear Derating Factor	(Notes 8 & 9)	P_D			
	(Notes 8 & 10)		1.7 13.6		
	(Notes 6 & 9)		83.3 51.0 111		°C/W
Thermal Resistance, Junction to Ambient	(Notes 7 & 9)	D			
Thermal Resistance, Junction to Ambient	(Notes 8 & 9)	$R_{\theta JA}$			
	(Notes 8 & 10)		73	73.5	
Thermal Resistance, Junction to Lead (Notes 9 & 11)		$R_{ heta JL}$	17.1		
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to	+150	°C	

Notes:

- 6. For a dual device surface mounted on 28mm x 28mm (8cm²) FR4 PCB with high coverage of single sided 2 oz copper, in still air conditions; the device is measured when operating in a steady-state condition. The heatsink is split in half with the exposed collector pads connected to each half.

 7. Same as Note (6), except the device is measured at t <5 sec.

 8. Same as Note (6), except the device is surface mounted on 31mm x 31mm (10cm²) FR4 PCB with high coverage of single sided 1oz copper.

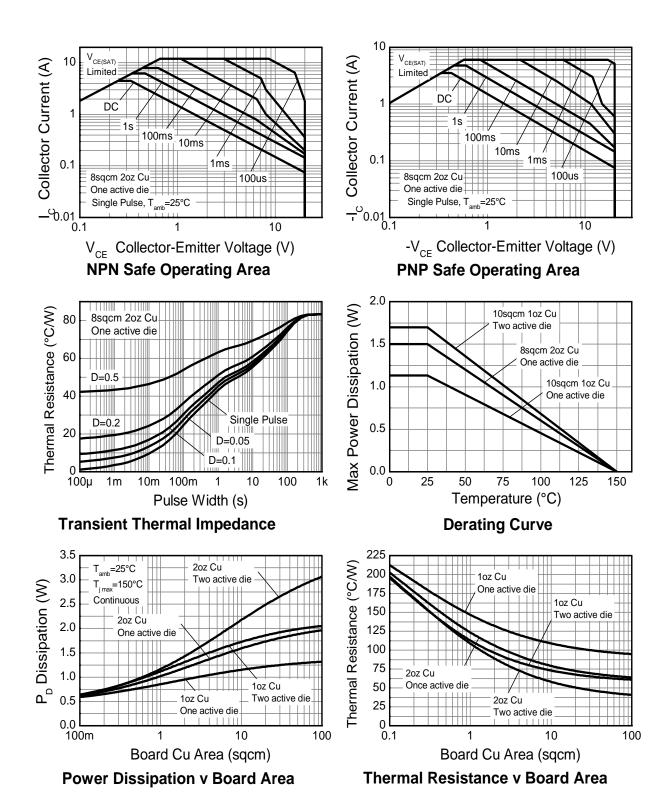
 9. For a dual device with one active die.

 10. For dual device with 2 active die running at equal power.

- 11. Thermal resistance from junction to solder-point (on the exposed collector pads).



Thermal Characteristics and Derating Information





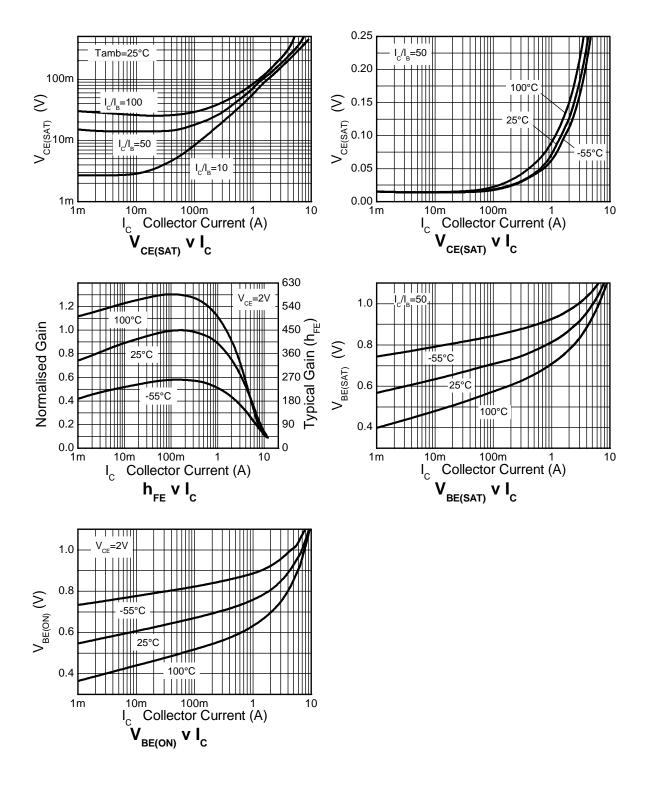
NPN - Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	40	100	_	V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage (Note 12)	BV _{CEO}	20	27	_	V	$I_C = 10mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.2	_	V	$I_{E} = 100 \mu A$
Collector Cutoff Current	I _{CBO}	_	_	100	nA	V _{CB} = 30V
Emitter Cutoff Current	I _{EBO}	_	_	100	nA	$V_{EB} = 6V$
Collector Emitter Cutoff Current	I _{CES}	_	_	100	nA	V _{CE} = 16V
Static Forward Current Transfer Ratio (Note 12)	h _{FE}	200 300 200 100	400 450 360 180		_	$I_{C} = 10mA, V_{CE} = 2V$ $I_{C} = 200mA, V_{CE} = 2V$ $I_{C} = 2A, V_{CE} = 2V$ $I_{C} = 6A, V_{CE} = 2V$
Collector-Emitter Saturation Voltage (Note 12)	V _{CE(SAT)}		8 90 115 190 210	15 150 135 250 300	mV	$\begin{split} &I_{C}=0.1\text{A},\ I_{B}=10\text{mA}\\ &I_{C}=1\text{A},\ I_{B}=10\text{mA}\\ &I_{C}=2\text{A},\ I_{B}=50\text{mA}\\ &I_{C}=3\text{A},\ I_{B}=100\text{mA}\\ &I_{C}=4.5\text{A},\ I_{B}=125\text{mA} \end{split}$
Base-Emitter Turn-On Voltage (Note 12)	V _{BE(ON)}	_	0.88	0.97	V	I _C = 4.5A, V _{CE} = 2V
Base-Emitter Saturation Voltage (Note 12)	V _{BE(SAT)}	_	0.98	1.07	V	I _C = 4.5A, I _B = 125mA
Output Capacitance	C _{OBO}	_	23	30	pF	V _{CB} = 10V, f = 1MHz
Transition Frequency	f _T	100	140	_	MHz	V _{CE} = 10V, I _C = 50mA, f = 100MHz
Turn-On Time	ton	_	170		ns	$V_{CC} = 10V, I_C = 3A$
Turn-Off Time	toff		400		ns	$I_{B1} = -I_{B2} = 10mA$

Note: 12. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



NPN - Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)





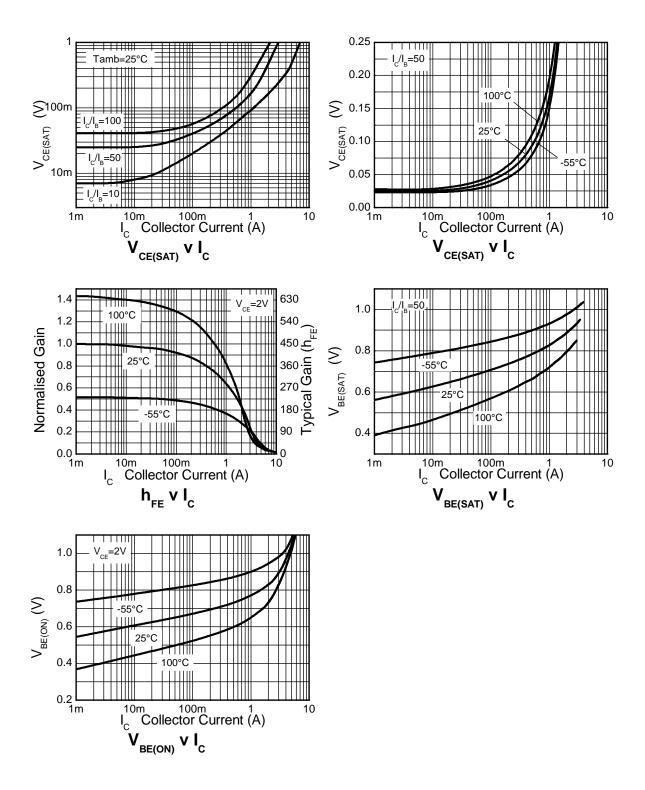
PNP - Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-25	-35	_	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 12)	BV _{CEO}	-20	-25	_	V	$I_C = -10 \text{mA}$
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-8.5	_	V	$I_E = -100 \mu A$
Collector Cutoff Current	I _{CBO}	_	_	-100	nA	V _{CB} = -20V
Emitter Cutoff Current	I _{EBO}		_	-100	nA	$V_{EB} = -6V$
Collector Emitter Cutoff Current	I _{CES}		_	-100	nA	V _{CES} = -16V
Static Forward Current Transfer Ratio (Note 12)	h _{FE}	300 300 150 15	475 450 230 30			I_{C} = -10mA, V_{CE} = -2V I_{C} = -100mA, V_{CE} = -2V I_{C} = -2A, V_{CE} = -2V I_{C} = -6A, V_{CE} = -2V
Collector-Emitter Saturation Voltage (Note 12)	V _{CE(SAT)}	_	-19 -170 -190 -240 -225	-30 -220 -250 -350 -300	mV	$\begin{split} &I_{C} = -0.1A,\ I_{B} = -10\text{mA} \\ &I_{C} = -1A,\ I_{B} = -20\text{mA} \\ &I_{C} = -1.5A,\ I_{B} = -50\text{mA} \\ &I_{C} = -2.5A,\ I_{B} = -150\text{mA} \\ &I_{C} = -3.5A,\ I_{B} = -350\text{mA} \end{split}$
Base-Emitter Turn-On Voltage (Note 12)	V _{BE(ON)}	_	-0.87	-0.95	V	I _C = -3.5A, V _{CE} = -2V
Base-Emitter Saturation Voltage (Note 12)	V _{BE(SAT)}	_	-1.01	-1.12	V	I _C = -3.5A, I _B = -350mA
Output Capacitance	C _{OBO}	_	21	30	pF	V _{CB} = -10V. f = 1MHz
Transition Frequency	f _T	150	180	_	MHz	V _{CE} = -10V, I _C = -50mA, f = 100MHz
Turn-On Time	t _{ON}	_	40	_	ns	V _{CC} = -10V, I _C = -1A
Turn-Off Time	toff	_	670		ns	$I_{B1} = -I_{B2} = -10 \text{mA}$

Note: 12. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



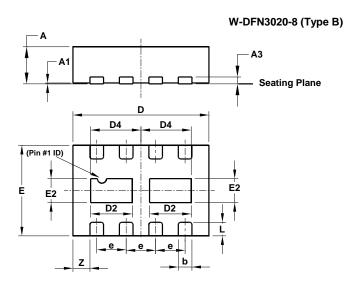
PNP - Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)





Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

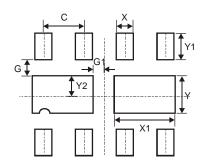


W-DFN3020-8						
(Type B)						
Dim	Min	Max	Тур			
Α	0.77	0.83	0.80			
A1	0	0.05	0.02			
A3	-	-	0.15			
b	0.25	0.35	0.30			
D	2.95	3.075	3.00			
D2	0.82	1.02	0.92			
D4	1.01	1.21	1.11			
е	-	-	0.65			
Е	1.95	2.075	2.00			
E2	0.43	0.63	0.53			
L	0.25	0.35	0.30			
Z	-	-	0.375			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

W-DFN3020-8 (Type B)



Dimensions	Value (in mm)
С	0.650
G	0.285
G1	0.090
Х	0.400
X1	1.120
Υ	0.730
Y1	0.500
Y2	0.365



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